

APPROVED	O.G. FIG.	
BY	CLASS	SUBCLASS
DRAFTSMAN		

BEST AVAILABLE COPY

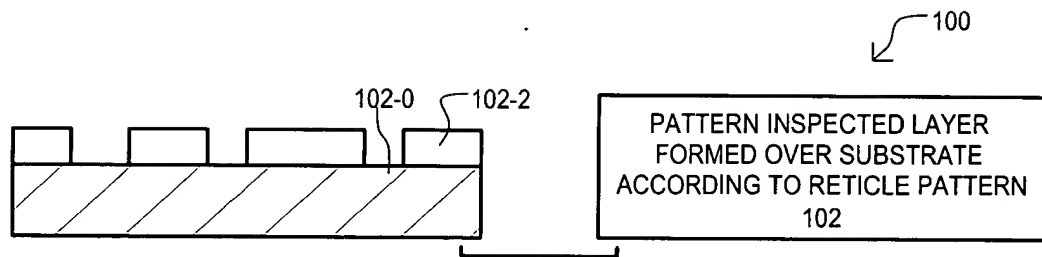


FIG. 1A

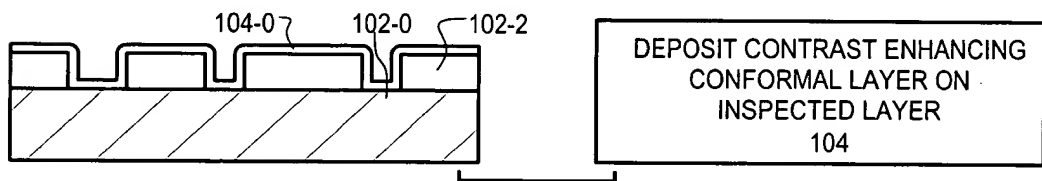


FIG. 1B

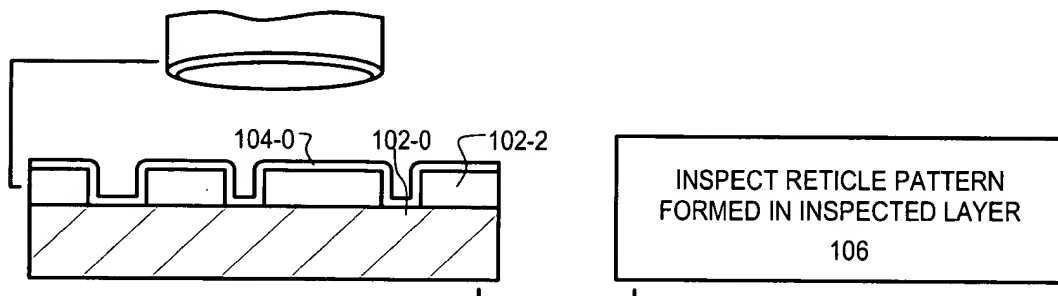
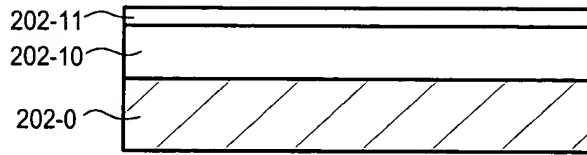


FIG. 1C

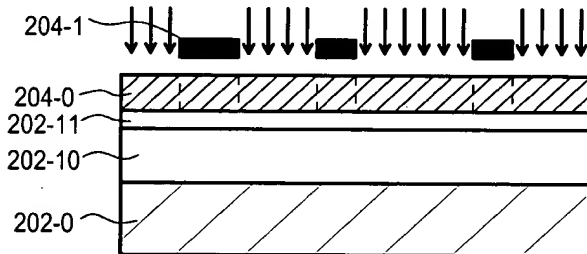
092034-07101

BEST AVAILABLE 200



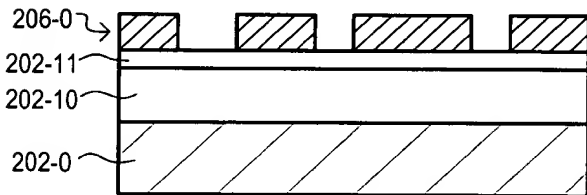
DEPOSIT NON-RESIST  
ETCHABLE LAYER(S)  
(ACCORDING TO MFG PROCESS  
FLOW)  
202

FIG. 2A



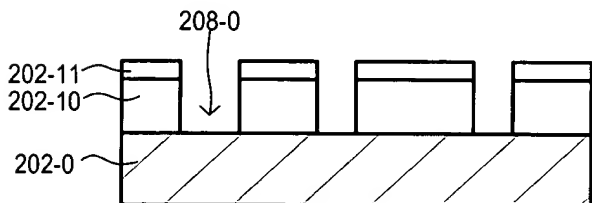
FORM AND DEVELOP RESIST OVER  
ETCHABLE LAYER(S) WITH  
RETICLE PATTERN  
204

FIG. 2B



PATTERN RESIST TO FORM  
ETCH MASK  
206

FIG. 2C



ETCH ETCHABLE LAYER  
ACCORDING TO  
RETICLE PATTERN  
208

FIG. 2D

0920374-073101

APPROVED	O.G. FIG.	
BY	CLASS	SUBCLASS
DRAFTSMAN		

BEST AVAILABLE COPY

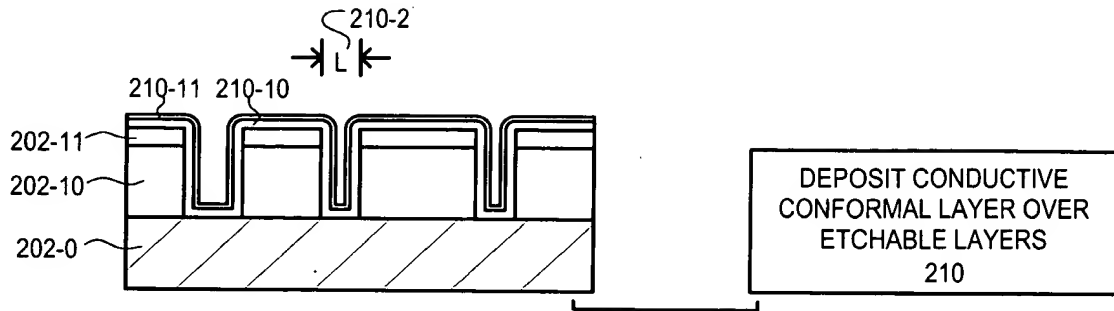


FIG. 2E

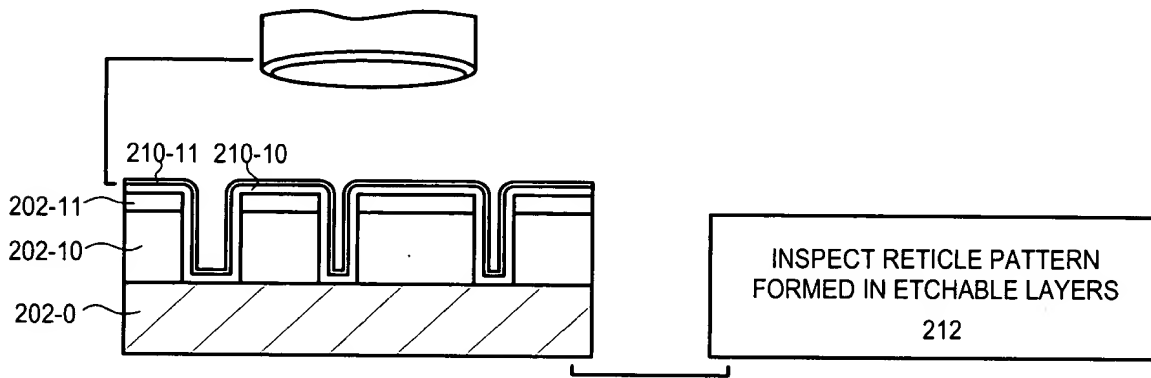
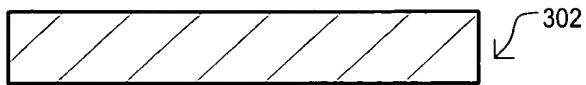


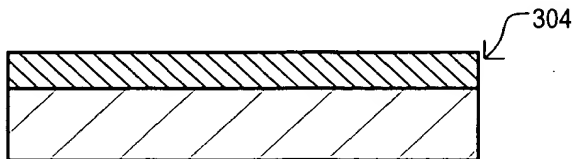
FIG. 2F

0920374.073101



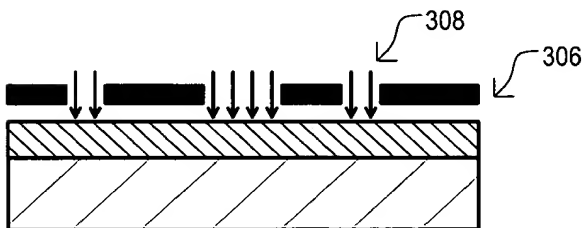
WAFER PREPARATION

FIG. 3A



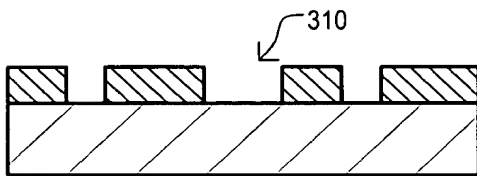
DEPOSIT RESIST

FIG. 3B



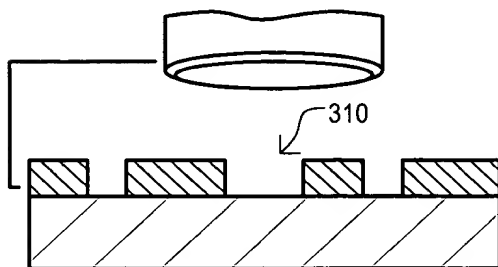
EXPOSE RESIST

FIG. 3C



DEVELOP RESIST

FIG. 3D



INSPECT RETICLE PATTERN  
FORMED IN RESIST LAYER

FIG. 3E

TOP SECRET